



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SA1627 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)

Collector current

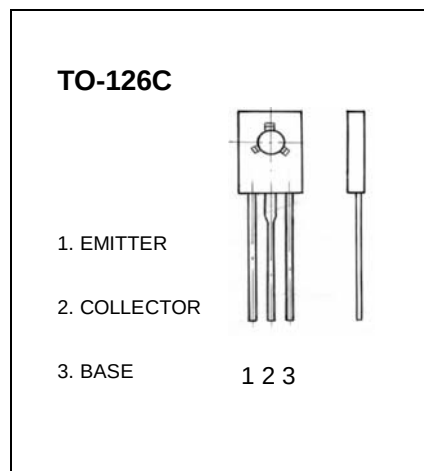
I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -600 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-600			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-600V, I_E=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			-10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-0.1A$	30		120	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-0.5A$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-300mA, I_B=-60mA$			-0.5	V
Base-emitter saturation voltage	$V_{B E(sat)}$	$I_C=-300mA, I_B=-60mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-100mA$	10			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			50	pF
Turn on time	t_{on}	$I_{B1}=-I_{B2}=-0.1A, I_C=-0.5A$ $V_{CC}=-250V, R_L=500\Omega$			0.5	μs
Fall time	t_f				5	μs
Storage time	t_s				0.5	μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	30-60	40-80	60-120

Typical Characteristics

2SA1627

